



# **isc Silicon NPN Power Transistor**

#### **DESCRIPTION**

- · Collector-Emilter Sustaining Voltage-
- : V<sub>CEO(SUS)</sub>= 500V(Min.)
- · Low Collector Saturation Voltage
  - : V<sub>CE(sat)</sub>= 1.0V(Max.)@ I<sub>C</sub>= 3A
- · High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

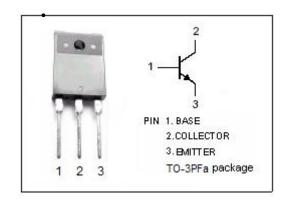


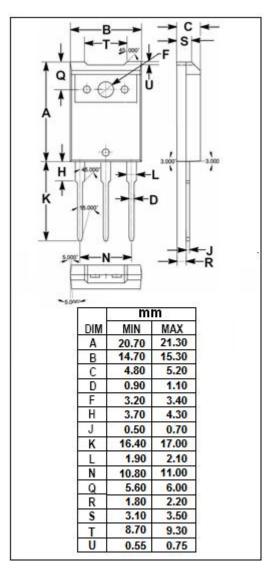
### **APPLICATIONS**

· Designed for high speed switching applications.

# ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>СВО</sub>	Collector-Base Voltage	800	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	500	V	
$V_{EBO}$	Emitter-Base Voltage	8	V	
Ic	Collector Current-Continuous	5	А	
Ісм	Collector Current-Peak	10	Α	
I <sub>B</sub>	Base Current-Continuous	3	А	
Pc	Collector Power Dissipation $@T_a=25^{\circ}C$	3	W	
	Collector Power Dissipation @T <sub>C</sub> =25°C	70		
T <sub>j</sub>	Junction Temperature 150		$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$	







## isc Silicon NPN Power Transistor

2SC3211

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> =30mA; I <sub>B</sub> = 0	500			V		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A			1.0	V		
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A			1.5	V		
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0			0.1	mA		
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			0.1	mA		
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	15					
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V	8					
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V		3		MHz		
Switching Times; Resistive Load								
t <sub>on</sub>	Turn-on Time				1.0	μS		
ts	Storage Time	I <sub>C</sub> = 3A; I <sub>B1</sub> = -I <sub>B2</sub> = 0.6A; V <sub>CC</sub> = 200V			3.0	μS		
tf	Fall Time				1.0	μs		

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